

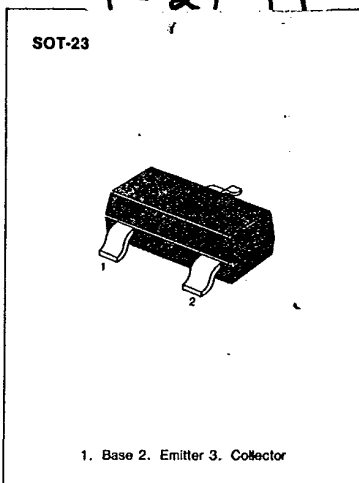
DRIVER TRANSISTOR

T-29-19

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CE0}	45	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	50	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C

• Refer to MMBT5086 for graphs



ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _C = 100μA, I _E = 0	50		V
Collector-Emitter Breakdown Voltage	BV _{CE0}	I _C = 1.0mA, I _B = 0	45		V
Emitter-Base Breakdown Voltage	BV _{EB0}	I _E = 10μA, I _C = 0	5		V
Collector Cutoff Current	I _{CB0}	V _{CB} = 4.0V, I _E = 0		50	nA
Emitter Cutoff Current	I _{EB0}	V _{EB} = 5.0V, I _C = 0		50	nA
DC Current Gain	h _{FE}	V _{CE} = 3V, I _C = 0.1mA	150		
		V _{CE} = 3V, I _C = 0.5mA	450	900	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 20mA, I _B = 2.0mA		0.3	V
Current Gain-Bandwidth Product	f _T	I _C = 1.0mA, V _{CE} = 6.0V f = 100MHz	75		MHz

3

Marking

